

# DDR2 SDRAM VLP Mini-RDIMM

MT9HVF6472(P)K – 512MB

MT9HVF12872(P)K – 1GB

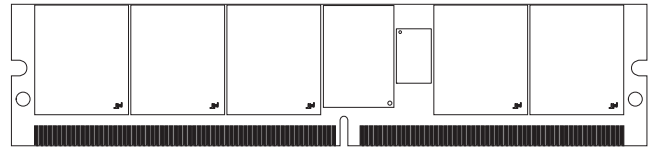
For component data sheets, refer to Micron's Web site: [www.micron.com](http://www.micron.com)

## Features

- 244-pin, very low profile mini registered dual in-line memory module (VLP Mini-RDIMM)
- Fast data transfer rates: PC2-3200, PC2-4200, PC2-5300, or PC2-6400
- 512MB (64 Meg x 72) or 1GB (128 Meg x 72)
- Supports ECC error detection and correction
- VDD = VDDQ = +1.8V
- VDDSPD = +1.7V to +3.6V
- JEDEC-standard 1.8V I/O (SSTL\_18-compatible)
- Differential data strobe (DQS, DQS#) option
- 4n-bit prefetch architecture
- Multiple internal device banks for concurrent operation
- Supports duplicate output strobe (RDQS/RDQS#)
- Programmable CAS# latency (CL)
- Posted CAS# additive latency (AL)
- WRITE latency = READ latency - 1 tCK
- Programmable burst lengths: 4 or 8
- Adjustable data-output drive strength
- 64ms, 8,192-cycle refresh
- On-die termination (ODT)
- Serial presence-detect (SPD) with EEPROM
- Gold edge contacts
- Single rank

Figure 1: 244-Pin VLP Mini-RDIMM

PCB height: 18.2mm (0.72in)



## Options

- Parity
- Operating temperature<sup>1</sup>
  - Commercial (0°C ≤ T<sub>A</sub> ≤ +70°C)
  - Industrial (-40°C ≤ T<sub>A</sub> ≤ +85°C)
- Package
  - 244-pin DIMM (Pb-free)
- Frequency/CAS latency<sup>2</sup>
  - 2.5ns @ CL = 5 (DDR2-800)
  - 2.5ns @ CL = 6 (DDR2-800)
  - 3ns @ CL = 5 (DDR2-667)
  - 3.75ns @ CL = 4 (DDR2-533)
  - 5.0ns @ CL = 3 (DDR2-400)
- PCB height
  - 18.2mm (0.72in)

## Marking

- P
- None
- I
- Y
- 80E
- 800
- 667
- 53E
- 40E

Notes: 1. Contact Micron for industrial temperature module offerings.

2. CL = CAS (READ) latency; registered mode will add one clock cycle to CL.

Table 1: Key Timing Parameters

Speed Grade	Industry Nomenclature	Data Rate (MT/s)				t <sub>RCD</sub> (ns)	t <sub>RP</sub> (ns)	t <sub>RC</sub> (ns)
		CL = 6	CL = 5	CL = 4	CL = 3			
-80E	PC2-6400	–	800	533	–	12.5	12.5	55
-800	PC2-6400	800	667	53E	–	15	15	55
-667	PC2-5300	–	667	533	400	15	15	55
-53E	PC2-4200	–	–	533	400	15	15	55
-40E	PC2-3200	–	–	400	400	15	15	55

**Table 2: Addressing**

	512MB	1GB
Refresh count	8K	8K
Row address	16K (A0–A13)	16K (A0–A13)
Device bank address	4 (BA0, BA1)	8 (BA0–BA2)
Device page size per bank	1KB	1KB
Device configuration	512Mb (64 Meg x 8)	1Gb (128 Meg x 8)
Column address	1K (A0–A9)	1K (A0–A9)
Module rank address	1 (S0#)	1 (S0#)

**Table 3: Part Numbers and Timing Parameters – 512MB Modules**

Base device: MT47H64M8,<sup>1</sup> 512Mb DDR2 SDRAM

Part Number <sup>2</sup>	Module Density	Configuration	Module Bandwidth	Memory Clock/ Data Rate	Latency (CL- <sup>t</sup> RCD- <sup>t</sup> RP)
MT9HVF6472(P)KY-80E__	512MB	64 Meg x 72	6.4 GB/s	2.5ns/800 MT/s	5-5-5
MT9HVF6472(P)KY-800__	512MB	64 Meg x 72	6.4 GB/s	2.5ns/800 MT/s	6-6-6
MT9HVF6472(P)KY-667__	512MB	64 Meg x 72	5.3 GB/s	3.0ns/667 MT/s	5-5-5
MT9HVF6472(P)KY-53E__	512MB	64 Meg x 72	4.3 GB/s	3.75ns/533 MT/s	4-4-4
MT9HVF6472(P)KY-40E__	512MB	64 Meg x 72	3.2 GB/s	5.0ns/400 MT/s	3-3-3

**Table 4: Part Numbers and Timing Parameters – 1GB Modules**

Base device: MT47H128M8,<sup>1</sup> 1Gb DDR2 SDRAM

Part Number <sup>2</sup>	Module Density	Configuration	Module Bandwidth	Memory Clock/ Data Rate	Latency (CL- <sup>t</sup> RCD- <sup>t</sup> RP)
MT9HVF12872(P)KY-80E__	1GB	128 Meg x 72	6.4 GB/s	2.5ns/800 MT/s	5-5-5
MT9HVF12872(P)KY-800__	1GB	128 Meg x 72	6.4 GB/s	2.5ns/800 MT/s	6-6-6
MT9HVF12872(P)KY-667__	1GB	128 Meg x 72	5.3 GB/s	3.0ns/667 MT/s	5-5-5
MT9HVF12872(P)KY-53E__	1GB	128 Meg x 72	4.3 GB/s	3.75ns/533 MT/s	4-4-4
MT9HVF12872(P)KY-40E__	1GB	128 Meg x 72	3.2 GB/s	5.0ns/400 MT/s	3-3-3

- Notes:
1. Data sheets for the base devices can be found on Micron's Web site.
  2. All part numbers end with a two-place code (not shown), designating component and PCB revisions. Consult factory for current revision codes. Example: MT9HVF12872KY-40EE1.



## Pin Assignments and Descriptions

Table 5: Pin Assignments

244-Pin VLP Mini-RDIMM Front								244-Pin VLP Mini-RDIMM Back							
Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol		
1	VREF	32	Vss	63	VDDQ	94	DQS5#	123	Vss	154	DQ28	185	A3	216	NC/ RDQS5#
2	Vss	33	DQ24	64	A2	95	DQS5	124	DQ4	155	DQ29	186	A1	217	Vss
3	DQ0	34	DQ25	65	VDD	96	Vss	125	DQ5	156	Vss	187	VDD	218	DQ46
4	DQ1	35	Vss	66	Vss	97	DQ42	126	Vss	157	DM3/ RDQS3	188	CK0	219	DQ47
5	Vss	36	DQS3#	67	Vss	98	DQ43	127	DM0/ RDQS0	158	NC/ RDQS3#	189	CK0#	220	Vss
6	DQS0#	37	DQS3	68 <sup>3</sup>	NC/ PAR_IN	99	Vss	128	NC/ RDQS0#	159	Vss	190	VDD	221	DQ52
7	DQS0	38	Vss	69	VDD	100	DQ48	129	Vss	160	DQ30	191	A0	222	DQ53
8	Vss	39	DQ26	70	A10	101	DQ49	130	DQ6	161	DQ31	192	BA1	223	Vss
9	DQ2	40	DQ27	71	BA0	102	Vss	131	DQ7	162	Vss	193	VDD	224	RFU
10	DQ3	41	Vss	72	VDD	103	SA2	132	Vss	163	CB4	194	RAS#	225	RFU
11	Vss	42	CB0	73	WE#	104	NC	133	DQ12	164	CB5	195	VDDQ	226	Vss
12	DQ8	43	CB1	74	VDDQ	105	Vss	134	DQ13	165	Vss	196	SO#	227	DM6/ RDQS6
13	DQ9	44	Vss	75	CAS#	106	DQS6#	135	Vss	166	DM8/ RDQS8	197	VDDQ	228	NC/ RDQS#6
14	Vss	45	DQS8#	76	VDDQ	107	DQS6	136	DM1/ RDQS1	167	NC/ RDQS8#	198	ODT0	229	Vss
15	DQS1#	46	DQS8	77	NC	108	Vss	137	NC/ RDQS1#	168	Vss	199	A13	230	DQ54
16	DQS1	47	Vss	78	NC	109	DQ50	138	Vss	169	CB6	200	VDD	231	DQ55
17	Vss	48	CB2	79	VDDQ	110	DQ51	139	RFU	170	CB7	201	NC	232	Vss
18	RESET#	49	CB3	80	NC	111	Vss	140	RFU	171	Vss	202	Vss	233	DQ60
19	NC	50	Vss	81	Vss	112	DQ56	141	Vss	172	NC	203	DQ36	234	DQ61
20	Vss	51	NC	82	DQ32	113	DQ57	142	DQ14	173	VDDQ	204	DQ37	235	Vss
21	DQ10	52	VDDQ	83	DQ33	114	Vss	143	DQ15	174	NC	205	Vss	236	DM7/ RDQS7
22	DQ11	53	CKE0	84	Vss	115	DQS7#	144	Vss	175	VDD	206	DM4/ RDQS4	237	NC/ RDQS7#
23	Vss	54	VDD	85	DQS4#	116	DQS7	145	DQ20	176	NC	207	NC/ RDQS4#	238	Vss
24	DQ16	55 <sup>1</sup>	NC/BA2	86	DQS4	117	Vss	146	DQ21	177	NC	208	Vss	239	DQ62
25	DQ17	56 <sup>2</sup>	NC/ ERR_OUT	87	Vss	118	DQ58	147	Vss	178	VDDQ	209	DQ38	240	DQ63
26	Vss	57	VDDQ	88	DQ34	119	DQ59	148	DM2/ RDQS2	179	A12	210	DQ39	241	Vss
27	DQS2#	58	A11	89	DQ35	120	Vss	149	NC/ RDQS2#	180	A9	211	Vss	242	SDA
28	DQS2	59	A7	90	Vss	121	SA0	150	Vss	181	VDD	212	DQ44	243	SCL
29	Vss	60	VDD	91	DQ40	122	SA1	151	DQ22	182	A8	213	DQ45	244	VDDSPD
30	DQ18	61	A5	92	DQ41			152	DQ23	183	A6	214	Vss		
31	DQ19	62	A4	93	Vss			153	Vss	184	VDDQ	215	DM5/ RDQS5		

- Notes:
1. Pin 55 is NC for 512MB, BA2 for 1GB.
  2. Pin 56 is NC for non-parity and ERR\_OUT for parity.
  3. Pin 68 is NC for non-parity and PAR\_IN for parity.

**Table 6: Pin Descriptions**

Symbol	Type	Description
ODT0	Input (SSTL_18)	<b>On-die termination:</b> ODT (registered HIGH) enables termination resistance internal to the DDR2 SDRAM. When enabled, ODT is only applied to each of the following pins: DQ, DQS, DQS#, RDQS, RDQS#, CB, and DM. The ODT input will be ignored if disabled via the LOAD MODE (LM) command.
CK0, CK0#	Input (SSTL_18)	<b>Clock:</b> CK and CK# are differential clock inputs. All address and control input signals are sampled on the crossing of the positive edge of CK and negative edge of CK#. Output data (DQs and DQS/DQS#) is referenced to the crossings of CK and CK#.
CKE0	Input (SSTL_18)	<b>Clock enable:</b> CKE (registered HIGH) activates and CKE (registered LOW) deactivates clocking circuitry on the DDR2 SDRAM.
S0#	Input (SSTL_18)	<b>Chip select:</b> S# enables (registered LOW) and disables (registered HIGH) the command decoder. All commands are masked when S# is registered HIGH. S# provides for external rank selection on systems with multiple ranks. S# is considered part of the command code.
RAS#, CAS#, WE#	Input (SSTL_18)	<b>Command inputs:</b> RAS#, CAS#, and WE# (along with S#) define the command being entered.
BA0, BA1 (512MB) BA0-BA2 (1GB)	Input (SSTL_18)	<b>Bank address inputs:</b> BA0-BA1/BA2 define to which device bank an ACTIVE, READ, WRITE, or PRECHARGE command is being applied. BA0-BA1/BA2 define which mode register, including MR, EMR, EMR(2), and EMR(3), is loaded during the LM command.
A0-A13	Input (SSTL_18)	<b>Address inputs:</b> Provide the row address for ACTIVE commands, and the column address and auto precharge bit (A10) for READ/WRITE commands, to select one location out of the memory array in the respective bank. A10 sampled during a PRECHARGE command determines whether the PRECHARGE applies to one device bank (A10 LOW, device bank selected by BA0-BA1/BA2) or all device banks (A10 HIGH). The address inputs also provide the op-code during a LM command.
PAR_IN	Input (SSTL_18)	Parity bit for the address and control bus.
SCL	Input (SSTL_18)	<b>Serial clock for presence-detect:</b> SCL is used to synchronize the presence-detect data transfer to and from the module.
SA0-SA2	Input (SSTL_18)	<b>Presence-detect address inputs:</b> These pins are used to configure the presence-detect device.
RESET#	Input (SSTL_18)	Asynchronously forces all registered outputs LOW when RESET# is LOW. This signal can be used during power-up to ensure that CKE is LOW and DQs are High-Z.
DQ0-DQ63	I/O (SSTL_18)	<b>Data input/output:</b> Bidirectional data bus.
DQS0-DQS8, DQS0#-DQS8#	I/O (SSTL_18)	<b>Data strobe:</b> Output with read data, input with write data for source synchronous operation. Edge-aligned with read data, center-aligned with write data. DQS# is only used when differential data strobe mode is enabled via the LM command. DQS9#-DQS17# are only used when RDQS# is enabled via the LM command.
DM0-DM8 (RDQS0-RDQS8)	I/O (SSTL_18)	<b>Input data mask:</b> DM is an input mask signal for write data. Input data is masked when DM is sampled HIGH along with that input data during a WRITE access. DM is sampled on both edges of DQS. Although DM pins are input-only, the DM loading is designed to match that of DQ and DQS pins. If RDQS is enabled, DQS0#-DQS8# are used only during the READ command. If RDQS is disabled, RDQS0-RDQS8 become DM0-DM8 and RDQS0#-RDQS8# are not used.
CB0-CB7	I/O (SSTL_18)	Check bits.
SDA	I/O (SSTL_18)	<b>Serial presence-detect data:</b> SDA is a bidirectional pin used to transfer addresses and data into and out of the presence-detect portion of the module.
ERR_OUT	Output (open drain)	Parity error found on the address and control bus.
VDD/VDDQ	Supply	<b>Power supply:</b> 1.8V ±0.1V.

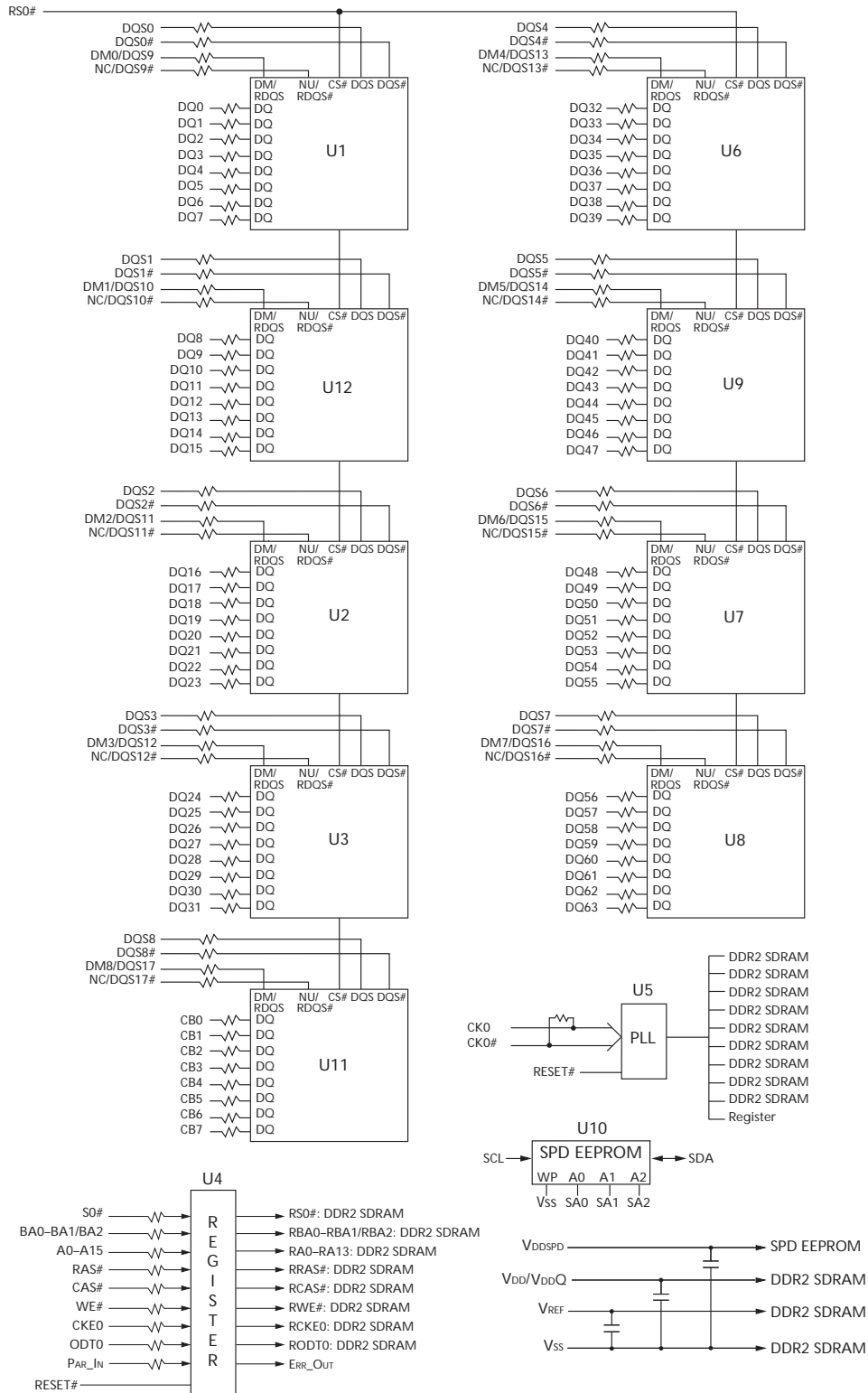


Table 6: Pin Descriptions (continued)

Symbol	Type	Description
VREF	Supply	SSTL_18 reference voltage.
VSS	Supply	Ground.
VDDSPD	Supply	<b>Serial EEPROM positive power supply:</b> +1.7V to +3.6V.
NC	-	<b>No connect:</b> These pins should be left unconnected.
RFU	-	Reserved for future use.

## Functional Block Diagram

Figure 2: Functional Block Diagram



## General Description

The MT9HVF6472(P)K and MT9HVF12872(P)K DDR2 SDRAM modules are high-speed, CMOS, dynamic random-access 512MB and 1GB memory modules organized in a x72 configuration. DDR2 SDRAM modules use internally configured 4-bank (512Mb) or 8-bank (1Gb) DDR2 SDRAM devices.

DDR2 SDRAM modules use double data rate architecture to achieve high-speed operation. The double data rate architecture is essentially a  $4n$ -prefetch architecture with an interface designed to transfer two data words per clock cycle at the I/O pins. A single read or write access for the DDR2 SDRAM module effectively consists of a single  $4n$ -bit-wide, one-clock-cycle data transfer at the internal DRAM core and four corresponding  $n$ -bit-wide, one-half-clock-cycle data transfers at the I/O pins.

A bidirectional data strobe (DQS, DQS#) is transmitted externally, along with data, for use in data capture at the receiver. DQS is a strobe transmitted by the DDR2 SDRAM device during READs and by the memory controller during WRITEs. DQS is edge-aligned with data for READs and center-aligned with data for WRITEs.

DDR2 SDRAM modules operate from a differential clock (CK and CK#); the crossing of CK going HIGH and CK# going LOW will be referred to as the positive edge of CK. Commands are registered at every positive edge of CK. Input data is registered on both edges of DQS, and output data is referenced to both edges of DQS, as well as to both edges of CK.

## Register and PLL Operation

DDR2 SDRAM modules operate in registered mode, where the command/address input signals are latched in the registers on the rising clock edge and sent to the DDR2 SDRAM devices on the following rising clock edge (data access is delayed by one clock cycle). A phase-lock loop (PLL) on the module receives and re-drives the differential clock signals (CK, CK#) to the DDR2 SDRAM devices. The register(s) and PLL reduce address, command, control, and clock signal loading by isolating DRAM from the system controller. PLL clock timing is defined by JEDEC specifications and ensured by use of the JEDEC clock reference board. Registered mode will add one clock cycle to CL.

## Serial Presence-Detect Operation

DDR2 SDRAM modules incorporate serial presence-detect (SPD). The SPD function is implemented using a 2,048-bit EEPROM. This nonvolatile storage device contains 256 bytes. The first 128 bytes are programmed by Micron to identify the module type and various SDRAM organizations and timing parameters. The remaining 128 bytes of storage are available for use by the customer. System READ/WRITE operations between the master (system logic) and the slave EEPROM device occur via a standard I<sup>2</sup>C bus using the DIMM's SCL (clock) and SDA (data) signals, together with SA (2:0), which provide eight unique DIMM/EEPROM addresses. Write protect (WP) is tied to VSS on the module, permanently disabling hardware write protect.

## Electrical Specifications

Stresses greater than those listed in Table 7 may cause permanent damage to the module. This is a stress rating only, and functional operation of the module at these or any other conditions above those indicated in each device's data sheet is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

**Table 7: Absolute Maximum Ratings**

Symbol	Parameter	Min	Max	Units	
VDD/VDDQ	VDD/VDDQ supply voltage relative to Vss	-0.5	+2.3	V	
VIN, VOUT	Voltage on any pin relative to Vss	-0.5	+2.3	V	
II	Input leakage current; Any input $0V \leq V_{IN} \leq V_{DD}$ ; VREF input $0V \leq V_{IN} \leq 0.95V$ (All other pins not under test = 0V)	Command/address RAS#, CAS#, WE#, S#, CKE, ODT, BA	-5	+5	$\mu A$
		CK, CK#	-250	+250	
		DM	-5	+5	
Ioz	Output leakage current; $0V \leq V_{OUT} \leq V_{DDQ}$ ; DQs and ODT are disabled	-5	+5	$\mu A$	
IVREF	VREF leakage current; VREF = valid VREF level	-18	+18	$\mu A$	
TA	Module ambient operating temperature	Commercial	0	+70	$^{\circ}C$
		Industrial	-40	+85	$^{\circ}C$
TC <sup>1</sup>	DDR2 SDRAM component case operating temperature <sup>2</sup>	Commercial	0	+85	$^{\circ}C$
		Industrial	-40	+95	$^{\circ}C$

- Notes: 1. Refresh rate is required to double when  $85^{\circ}C < T_C \leq 95^{\circ}C$ .  
2. For further information, refer to technical note [TN-00-08: Thermal Applications](#), available on Micron's Web site.

## Input Capacitance

Micron encourages designers to simulate the performance of the module to achieve optimum values. Simulations are significantly more accurate and realistic than a gross estimation of module capacitance when inductance and delay parameters associated with trace lengths are used in simulations. JEDEC modules are currently designed using simulations to close timing budgets.

## Component AC Operating Specifications

Recommended AC operating conditions are given in the DDR2 component data sheets. Component specifications are available on Micron's Web site. Module speed grades correlate with component speed grades as shown in Table 8.

**Table 8: Module and Component Speed Grades**

Module Speed Grade	Component Speed Grade
-80E	-25E
-800	-25
-667	-3
-53E	-37E
-40E	-5E



## IDD Specifications

**Table 9: IDD Specifications and Conditions – 512MB**

Values shown for MT47H64M8 DDR2 SDRAM only and are computed from values specified in the 512Mb (64 Meg x 8) component data sheet

Parameter/Condition	Symbol	-80E -800	-667	-53E	-40E	Units	
<b>Operating one bank active-precharge current:</b> $t_{CK} = t_{CK} (IDD)$ , $t_{RC} = t_{RC} (IDD)$ , $t_{RAS} = t_{RAS} MIN (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	IDD0	900	810	720	720	mA	
<b>Operating one bank active-read-precharge current:</b> $I_{OUT} = 0mA$ ; BL = 4, CL = CL (IDD), AL = 0; $t_{CK} = t_{CK} (IDD)$ , $t_{RC} = t_{RC} (IDD)$ , $t_{RAS} = t_{RAS} MIN (IDD)$ , $t_{RCD} = t_{RCD} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data pattern is same as IDD4W	IDD1	1,035	945	855	810	mA	
<b>Precharge power-down current:</b> All device banks idle; $t_{CK} = t_{CK} (IDD)$ ; CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating	IDD2P	63	63	63	63	mA	
<b>Precharge quiet standby current:</b> All device banks idle; $t_{CK} = t_{CK} (IDD)$ ; CKE is HIGH, S# is HIGH; Other control and address bus inputs are stable; Data bus inputs are floating	IDD2Q	450	405	360	315	mA	
<b>Precharge standby current:</b> All device banks idle; $t_{CK} = t_{CK} (IDD)$ ; CKE is HIGH, S# is HIGH; Other control and address bus inputs are switching; Data bus inputs are switching	IDD2N	495	450	405	360	mA	
<b>Active power-down current:</b> All device banks open; $t_{CK} = t_{CK} (IDD)$ ; CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating	Fast PDN exit MR[12] = 0	IDD3P	360	315	270	225	mA
		Slow PDN exit MR[12] = 1	108	108	108	108	mA
<b>Active standby current:</b> All device banks open; $t_{CK} = t_{CK} (IDD)$ , $t_{RAS} = t_{RAS} MAX (IDD)$ , $t_{RP} = t_{RP} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching	IDD3N	630	585	495	405	mA	
<b>Operating burst write current:</b> All device banks open; Continuous burst writes; BL = 4, CL = CL (IDD), AL = 0; $t_{CK} = t_{CK} (IDD)$ , $t_{RAS} = t_{RAS} MAX (IDD)$ , $t_{RP} = t_{RP} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	IDD4W	1,755	1,530	1,260	1,035	mA	
<b>Operating burst read current:</b> All device banks open; Continuous burst reads; $I_{OUT} = 0mA$ ; BL = 4, CL = CL (IDD), AL = 0; $t_{CK} = t_{CK} (IDD)$ , $t_{RAS} = t_{RAS} MAX (IDD)$ , $t_{RP} = t_{RP} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	IDD4R	1,845	1,620	1,305	1,035	mA	
<b>Burst refresh current:</b> $t_{CK} = t_{CK} (IDD)$ ; REFRESH command at every $t_{RFC} (IDD)$ interval; CKE is HIGH, S# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching	IDD5	2,070	1,620	1,530	1,485	mA	
<b>Self refresh current:</b> CK and CK# at 0V; CKE $\leq 0.2V$ ; Other control and address bus inputs are floating; Data bus inputs are floating	IDD6	63	63	63	63	mA	
<b>Operating bank interleave read current:</b> All device banks interleaving reads; $I_{OUT} = 0mA$ ; BL = 4, CL = CL (IDD), AL = $t_{RCD} (IDD) - 1 \times t_{CK} (IDD)$ ; $t_{CK} = t_{CK} (IDD)$ , $t_{RC} = t_{RC} (IDD)$ , $t_{RRD} = t_{RRD} (IDD)$ , $t_{RCD} = t_{RCD} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are stable during deselects; Data bus inputs are switching	IDD7	2,700	2,160	2,025	1,980	mA	

**Table 10: IDD Specifications and Conditions – 1GB**

Values shown for MT47H128M8 DDR2 SDRAM only and are computed from values specified in the 1Gb (128 Meg x 8) component data sheet

Parameter/Condition	Symbol	-80E-800	-667	-53E	-40E	Units
<b>Operating one bank active-precharge current:</b> $t_{CK} = t_{CK} (IDD)$ , $t_{RC} = t_{RC} (IDD)$ , $t_{RAS} = t_{RAS} \text{ MIN} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	IDD0	810	765	630	630	mA
<b>Operating one bank active-read-precharge current:</b> $I_{OUT} = 0\text{mA}$ ; BL = 4, CL = CL (IDD), AL = 0; $t_{CK} = t_{CK} (IDD)$ , $t_{RC} = t_{RC} (IDD)$ , $t_{RAS} = t_{RAS} \text{ MIN} (IDD)$ , $t_{RCD} = t_{RCD} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data pattern is same as IDD4W	IDD1	990	900	855	810	mA
<b>Precharge power-down current:</b> All device banks idle; $t_{CK} = t_{CK} (IDD)$ ; CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating	IDD2P	63	63	63	63	mA
<b>Precharge quiet standby current:</b> All device banks idle; $t_{CK} = t_{CK} (IDD)$ ; CKE is HIGH, S# is HIGH; Other control and address bus inputs are stable; Data bus inputs are floating	IDD2Q	450	360	360	315	mA
<b>Precharge standby current:</b> All device banks idle; $t_{CK} = t_{CK} (IDD)$ ; CKE is HIGH, S# is HIGH; Other control and address bus inputs are switching; Data bus inputs are switching	IDD2N	450	360	360	315	mA
<b>Active power-down current:</b> All device banks open; $t_{CK} = t_{CK} (IDD)$ ; CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating	Fast PDN exit MR[12] = 0	IDD3P	360	270	270	mA
		Slow PDN exit MR[12] = 1	90	90	90	90
<b>Active standby current:</b> All device banks open; $t_{CK} = t_{CK} (IDD)$ , $t_{RAS} = t_{RAS} \text{ MAX} (IDD)$ , $t_{RP} = t_{RP} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching	IDD3N	540	495	405	360	mA
<b>Operating burst write current:</b> All device banks open; Continuous burst writes; BL = 4, CL = CL (IDD), AL = 0; $t_{CK} = t_{CK} (IDD)$ , $t_{RAS} = t_{RAS} \text{ MAX} (IDD)$ , $t_{RP} = t_{RP} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	IDD4W	1,440	1,215	1,125	945	mA
<b>Operating burst read current:</b> All device banks open; Continuous burst reads; $I_{OUT} = 0\text{mA}$ ; BL = 4, CL = CL (IDD), AL = 0; $t_{CK} = t_{CK} (IDD)$ , $t_{RAS} = t_{RAS} \text{ MAX} (IDD)$ , $t_{RP} = t_{RP} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	IDD4R	1,440	1,215	1,125	945	mA
<b>Burst refresh current:</b> $t_{CK} = t_{CK} (IDD)$ ; REFRESH command at every $t_{RFC} (IDD)$ interval; CKE is HIGH, S# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching	IDD5	2,115	1,935	1,890	1,845	mA
<b>Self refresh current:</b> CK and CK# at 0V; CKE $\leq 0.2\text{V}$ ; Other control and address bus inputs are floating; Data bus inputs are floating	IDD6	63	63	63	63	mA
<b>Operating bank interleave read current:</b> All device banks interleaving reads; $I_{OUT} = 0\text{mA}$ ; BL = 4, CL = CL (IDD), AL = $t_{RCD} (IDD) - 1 \times t_{CK} (IDD)$ ; $t_{CK} = t_{CK} (IDD)$ , $t_{RC} = t_{RC} (IDD)$ , $t_{RRD} = t_{RRD} (IDD)$ , $t_{RCD} = t_{RCD} (IDD)$ ; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are stable during deselects; Data bus inputs are switching	IDD7	3,015	2,520	2,430	2,340	mA

## Register and PLL Specifications

**Table 11: Register Specifications**  
SSTU32865 device or equivalent JESD82-19

Parameter	Symbol	Pins	Condition	Min	Max	Units
DC high-level input voltage	V <sub>IH(DC)</sub>	Address, control, command	SSTL_18	V <sub>REF(DC)</sub> + 125	V <sub>DDQ</sub> + 250	mV
DC low-level input voltage	V <sub>IL(DC)</sub>	Address, control, command	SSTL_18	0	V <sub>REF(DC)</sub> - 125	mV
AC high-level input voltage	V <sub>IH(AC)</sub>	Address, control, command	SSTL_18	V <sub>REF(DC)</sub> + 250	V <sub>DD</sub>	mV
AC low-level input voltage	V <sub>IL(AC)</sub>	Address, control, command	SSTL_18	0	V <sub>REF(DC)</sub> - 250	mV
Output high voltage	V <sub>OH</sub>	Parity output	LVC MOS	1.2	-	V
Output low voltage	V <sub>OL</sub>	Parity output	LVC MOS	-	0.5	V
Input current	I <sub>I</sub>	All pins	V <sub>I</sub> = V <sub>DDQ</sub> or V <sub>SSQ</sub>	-5	+5	μA
Static standby	I <sub>DD</sub>	All pins	RESET# = V <sub>SSQ</sub> (I <sub>O</sub> = 0)	-	200	μA
Static operating	I <sub>DD</sub>	All pins	RESET# = V <sub>SSQ</sub> ; V <sub>I</sub> = V <sub>IH(AC)</sub> or V <sub>IL(DC)</sub> I <sub>O</sub> = 0	-	80	mA
Dynamic operating (clock tree)	I <sub>DDD</sub>	n/a	RESET# = V <sub>DD</sub> , V <sub>I</sub> = V <sub>IH(AC)</sub> or V <sub>IL(AC)</sub> , I <sub>O</sub> = 0; CK and CK# switching 50% duty cycle	-	Varies by manufacturer	μA
Dynamic operating (per each input)	I <sub>DDD</sub>	n/a	RESET# = V <sub>DD</sub> , V <sub>I</sub> = V <sub>IH(AC)</sub> or V <sub>IL(AC)</sub> , I <sub>O</sub> = 0; CK and CK# switching 50% duty cycle; One data input switching at <sup>t</sup> CK/2, 50% duty cycle	-	Varies by manufacturer	μA
Input capacitance (per device, per pin)	C <sub>I</sub>	All inputs except RESET#	V <sub>I</sub> = V <sub>REF</sub> ±250mV; V <sub>DDQ</sub> = 1.8V	2.5	3.5	pF
Input capacitance (per device, per pin)	C <sub>I</sub>	RESET#	V <sub>I</sub> = V <sub>DDQ</sub> or V <sub>SSQ</sub>	-	Varies by manufacturer	pF

Notes: 1. Timing and switching specifications for the register listed above are critical for proper operation of the DDR2 SDRAM registered DIMMs. These are meant to be a subset of the parameters for the specific device used on the module. Detailed information for this register is available in JEDEC standard JESD82.

**Table 12: PLL Specifications**  
 CU877 device or equivalent JESD82-8.01

Parameter	Symbol	Pins	Condition	Min	Max	Units
DC high-level input voltage	V <sub>IH</sub>	RESET#	LVC MOS	0.65 × V <sub>DD</sub>	–	V
DC low-level input voltage	V <sub>IL</sub>	RESET#	LVC MOS	–	0.35 × V <sub>DD</sub>	V
Input voltage (limits)	V <sub>IN</sub>	RESET#, CK, CK#		–0.3	V <sub>DDQ</sub> + 0.3	V
DC high-level input voltage	V <sub>IH</sub>	CK, CK#	Differential input	0.65 × V <sub>DD</sub>	–	V
DC low-level input voltage	V <sub>IL</sub>	CK, CK#	Differential input	–	0.35 × V <sub>DD</sub>	V
Input differential-pair cross voltage	V <sub>IX</sub>	CK, CK#	Differential input	(V <sub>DDQ</sub> /2) - 0.15	(V <sub>DDQ</sub> /2) + 0.15	V
Input differential voltage	V <sub>ID(DC)</sub>	CK, CK#	Differential input	0.3	V <sub>DDQ</sub> + 0.4	V
Input differential voltage	V <sub>ID(AC)</sub>	CK, CK#	Differential input	0.6	V <sub>DDQ</sub> + 0.4	V
Input current	I <sub>I</sub>	RESET#	V <sub>I</sub> = V <sub>DDQ</sub> or V <sub>SSQ</sub>	–10	10	μA
		CK, CK#	V <sub>I</sub> = V <sub>DDQ</sub> or V <sub>SSQ</sub>	–250	250	μA
Output current	I <sub>ODL</sub>		RESET# = V <sub>SSQ</sub> ; V <sub>I</sub> = V <sub>IH(AC)</sub> or V <sub>IL(DC)</sub>	100	–	μA
Static supply current	I <sub>DDLD</sub>		CK = CK# = LOW	–	500	μA
Dynamic supply	I <sub>DD</sub>	n/a	CK, CK# = 270 MHz, all outputs open (not connected to PCB)	–	300	mA
Input capacitance	C <sub>IN</sub>	Each input	V <sub>I</sub> = V <sub>DDQ</sub> or V <sub>SSQ</sub>	2	3	pF

**Table 13: PLL Clock Driver Timing Requirements and Switching Characteristics**

Parameter	Symbol	Min	Max	Units
Stabilization time	t <sub>L</sub>	–	15	μs
Input clock slew rate	t <sub>LS1</sub>	1.0	4	V/ns
SSC modulation frequency		30	33	kHz
SSC clock input frequency deviation		0.0	–0.50	%
PLL loop bandwidth (–3dB from unity gain)		2.0	–	MHz

Notes: 1. PLL timing and switching specifications are critical for proper operation of the DDR2 DIMM. This is a subset of parameters for the specific PLL used. Detailed PLL information is available in JEDEC standard JESD82.

**Table 14: Serial Presence-Detect EEPROM DC Operating Conditions**

All voltages referenced to VSS; VDDSPD = +1.7V to +3.6V

Parameter/Condition	Symbol	Min	Max	Units
Supply voltage	VDDSPD	1.7	3.6	V
Input high voltage: Logic 1; All inputs	V <sub>IH</sub>	VDDSPD × 0.7	VDDSPD + 0.5	V
Input low voltage: Logic 0; All inputs	V <sub>IL</sub>	-0.6	VDDSPD × 0.3	V
Output low voltage: I <sub>OUT</sub> = 3mA	V <sub>OL</sub>	-	0.4	V
Input leakage current: V <sub>IN</sub> = GND to VDDSPD	I <sub>LI</sub>	0.10	3	μA
Output leakage current: V <sub>OUT</sub> = GND to VDDSPD	I <sub>LO</sub>	0.05	3	μA
Standby current	I <sub>SB</sub>	1.6	4	μA
Power supply current, READ: SCL clock frequency = 100 kHz	I <sub>CC<sub>R</sub></sub>	0.4	1	mA
Power supply current, WRITE: SCL clock frequency = 100 kHz	I <sub>CC<sub>W</sub></sub>	2	3	mA

**Table 15: Serial Presence-Detect EEPROM AC Operating Conditions**

All voltages referenced to VSS; VDDSPD = +1.7V to +3.6V

Parameter/Condition	Symbol	Min	Max	Units	Notes
SCL LOW to SDA data-out valid	t <sup>AA</sup>	0.2	0.9	μs	1
Time the bus must be free before a new transition can start	t <sup>BUF</sup>	1.3	-	μs	
Data-out hold time	t <sup>DH</sup>	200	-	ns	
SDA and SCL fall time	t <sup>F</sup>	-	300	ns	2
Data-in hold time	t <sup>HD:DAT</sup>	0	-	μs	
Start condition hold time	t <sup>HD:STA</sup>	0.6	-	μs	
Clock HIGH period	t <sup>HIGH</sup>	0.6	-	μs	
Noise suppression time constant at SCL, SDA inputs	t <sup>I</sup>	-	50	ns	
Clock LOW period	t <sup>LOW</sup>	1.3	-	μs	
SDA and SCL rise time	t <sup>R</sup>	-	0.3	μs	2
SCL clock frequency	f <sup>SCL</sup>	-	400	kHz	
Data-in setup time	t <sup>SU:DAT</sup>	100	-	ns	
Start condition setup time	t <sup>SU:STA</sup>	0.6	-	μs	3
Stop condition setup time	t <sup>SU:STO</sup>	0.6	-	μs	
WRITE cycle time	t <sup>WRC</sup>	-	10	ms	4

- Notes:
1. To avoid spurious start and stop conditions, a minimum delay is placed between SCL = 1 and the falling or rising edge of SDA.
  2. This parameter is sampled.
  3. For a restart condition, or following a WRITE cycle.
  4. The SPD EEPROM WRITE cycle time (t<sup>WRC</sup>) is the time from a valid stop condition of a write sequence to the end of the EEPROM internal ERASE/PROGRAM cycle. During the WRITE cycle, the EEPROM bus interface circuit is disabled, SDA remains HIGH due to pull-up resistance, and the EEPROM does not respond to its slave address.



## 512MB, 1GB: (x72, ECC, SR) 244-Pin DDR2 VLP Mini-RDIMM Register and PLL Specifications

**Table 16: Serial Presence-Detect Matrix**

Byte	Description	Entry (Version)	512MB	1GB
0	Number of SPD bytes used by Micron	128	80	80
1	Total number of bytes in SPD device	256	08	08
2	Fundamental memory type	DDR2 SDRAM	08	08
3	Number of row addresses on assembly	14	0E	0E
4	Number of column addresses on assembly	10	0A	0A
5	DIMM height and module ranks	18.2mm, single rank	00	00
6	Module data width	72	48	48
7	Reserved	0	00	00
8	Module voltage interface levels	SSTL 1.8V	05	05
9	SDRAM cycle time, <sup>t</sup> CK (CL = MAX value, see byte 18)	-80E/-800 -667 -53E -40E	25 30 3D 50	25 30 3D 50
10	SDRAM access from clock, <sup>t</sup> AC (CL = MAX value, see byte 18)	-80E/-800 -667 -53E -40E	40 45 50 60	40 45 50 60
11	Module configuration type	ECC ECC and parity	02 06	02 06
12	Refresh rate/type	7.81µs/SELF	82	82
13	SDRAM device width (primary SDRAM)	8	08	08
14	Error-checking SDRAM data width	8	08	08
15	Reserved	0	00	00
16	Burst lengths supported	4, 8	0C	0C
17	Number of banks on SDRAM device	4 or 8	04	08
18	CAS latencies supported	-80E (5, 4) -800 (6, 5, 4) -667 (5, 4, 3) -53E/-40E (4, 3)	30 70 38 18	30 70 38 18
19	Module thickness		01	01
20	DDR2 DIMM type	Registered Mini-RDIMM	10	10
21	SDRAM module attributes	1 PLL, 2 Reg	04	04
22	SDRAM device attributes: weak driver (01) and 50Ω ODT (03)	-80E/-800/-667 -53E/-40E	03 01	03 01
23	SDRAM cycle time, <sup>t</sup> CK, MAX CL - 1	-80E/-667 -800 -53E/-40E	3D 30 50	3D 30 50
24	SDRAM access from CK, <sup>t</sup> AC, MAX CL - 1	-80E/-800 -667 -53E -40E	40 45 50 60	40 45 50 60
25	SDRAM cycle time, <sup>t</sup> CK, MAX CL - 2	-80E/-800 -667 -53E/-40E	00/3D 50 00	00/3D 50 00
26	SDRAM access from CK, <sup>t</sup> AC, MAX CL - 2	-80E/-800 -667 -53E/-40E	00/40 45 00	00/40 45 00



Table 16: Serial Presence-Detect Matrix (continued)

Byte	Description	Entry (Version)	512MB	1GB
27	MIN row precharge time, $t_{RP}$	-80E -800/-667/-53E/-40E	32 3C	32 3C
28	MIN row active-to-row active, $t_{RRD}$		1E	1E
29	MIN RAS#-to-CAS# delay, $t_{RCD}$	-80E -800/-667/-53E/-40E	32 3C	32 3C
30	MIN active-to-precharge time, $t_{RAS}$	-80E/-800/-667/-53E -40E	2D 28	2D 28
31	Module rank density	512MB, 1GB	80	01
32	Address and command setup time, $t_{IS_b}$	-80E/-800 -667 -53E -40E	17 20 25 35	17 20 25 35
33	Address and command hold time, $t_{IH_b}$	-80E/-800 -667 -53E -40E	25 27 37 47	25 27 37 47
34	Data/data mask input setup time, $t_{DS_b}$	-80E/-800 -667/-53E -40E	05 10 15	05 10 15
35	Data/data mask input hold time, $t_{DH_b}$	-80E/-800 -667 -53E -40E	12 17 22 27	12 17 22 27
36	Write recovery time, $t_{WR}$		3C	3C
37	WRITE-to-READ command delay, $t_{WTR}$	-80E -800/-40E -667/-53E	1E 28 1E	1E 28 1E
38	READ-to-PRECHARGE command delay, $t_{RTP}$		1E	1E
39	Memory analysis probe		00	00
40	Extension for bytes 41 and 42	-80E -800/-667/-53E/-40E	30 00	36 06
41	MIN active-to-active/refresh time, $t_{RC}^1$	-80E -800/-667/-53E -40E	39 3C 37	39 3C 37
42	MIN AUTO REFRESH-to-ACTIVE/AUTO REFRESH command period, $t_{RFC}$		69	7F
43	SDRAM device MAX cycle time, $t_{CK} (MAX)$		80	80
44	SDRAM device MAX DQS-DQ skew time, $t_{DQSQ}$	-80E/-800 -667 -53E -40E	14 18 1E 23	14 18 1E 23
45	SDRAM device MAX read data hold skew factor, $t_{QHS}$	-80E/-800 -667 -53E -40E	1E 22 28 2D	1E 22 28 2D
46	PLL relock time		0F	0F
47-61	Optional features, not supported		00	00
62	SPD revision	Release 1.2	12	12



Table 16: Serial Presence-Detect Matrix (continued)

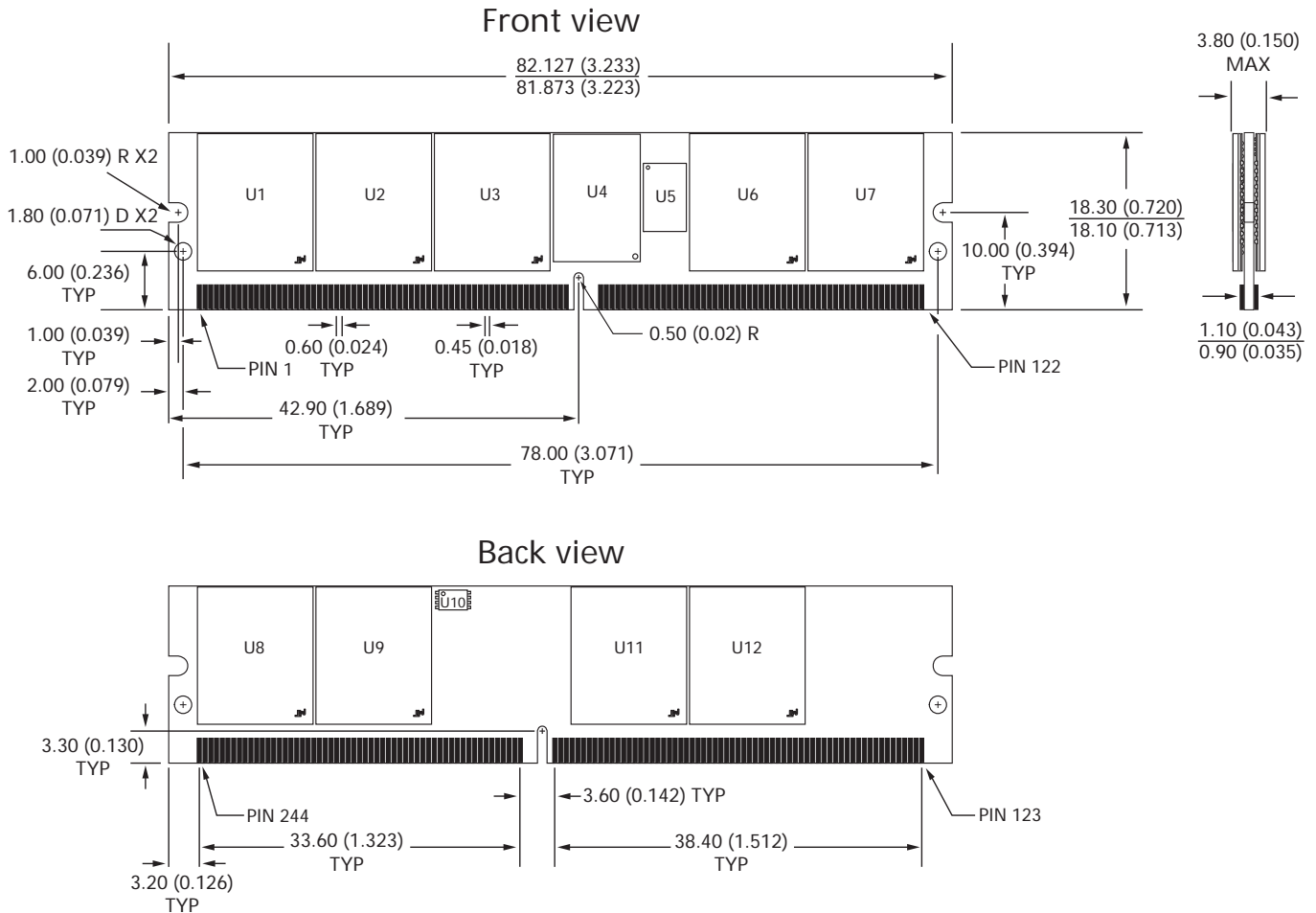
Byte	Description	Entry (Version)	512MB	1GB
63	Checksum for bytes 0-62 ECC/ECC and parity	-80E -800 -667 -53E -40E	62/66 03/07 1E/22 C9/CD 30/34	03/07 A4/A8 BF/C3 6A/6E D1/D5
64	Manufacturer's JEDEC ID code	MICRON	2C	2C
65-71	Manufacturer's JEDEC ID code	(continued)	FF	FF
72	Manufacturing location	1-12	01-0C	01-0C
73-90	Module part number (ASCII)	-	Variable data	Variable data
91	PCB identification code	1-9	01-09	01-09
92	Identification code (continued)	0	00	00
93	Year of manufacture in BCD	-	Variable data	Variable data
94	Week of manufacture in BCD	-	Variable data	Variable data
95-98	Module serial number	-	Variable data	Variable data
99-127	Reserved for manufacturer-specific data		00	00
128-255	Reserved for customer-specific data		FF	FF

Notes: 1. The <sup>t</sup>RC SPD values shown are JEDEC DDR2 device specification values. The actual Micron DDR2 device specification is <sup>t</sup>RC = 55ns for all speed grades.



## Module Dimensions

Figure 3: 244-Pin DDR2 VLP Mini-RDIMM



- Notes: 1. All dimensions are in millimeters (inches); MAX/MIN or typical (TYP) where noted.  
2. The dimensional diagram is for reference only. Refer to the JEDEC MO document for complete design dimensions.



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